

To: Solid State Electronics Editorial Board
Subject: Article Submit

Dear Editors,

Enclosed with this letter you will find an electronic submission of manuscript entitled “Influence of γ -irradiation and ultrasound treatment on carrier transport in Au-SiO₂-Si structure” by A. Gorb, O. Korotchenkov, O. Olikh, A. Podolian, and R. Chupryna. This is an original paper which has not simultaneously in whole or in part been submitted anywhere else. No conflict of interest exists in the submission of this manuscript.

It is known that the electrical properties of semiconductor devices are determined by the crystal microstructure. The present manuscript focused on silicon MOS structure, one of the most common forms of electronic devices used in application. It has been experimentally observed that ultrasound treatment leads to radiation defect annealing and recovering of γ -degraded silicon MOS structure characteristics. We believe that using ultrasound for defect engineering would be of interest to the journal's readers.

We would very much appreciate if you would consider the manuscript for publication in the *Solid State Electronics*.

Sincerely yours,
Oleg Olikh and co-authors
Taras Shevchenko National University of Kyiv
Kyiv 01601, Ukraine
E-mail: olikh@univ.kiev.ua